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# 16-Mbit (2M words × 8 bits) Static RAM with Error-Correcting Code (ECC)

## Features

- Ultra-low standby power
  - Typical standby current: 5.5  $\mu$ A
  - Maximum standby current: 16  $\mu$ A
- High speed: 45 ns/55 ns
- Embedded error-correcting code (ECC) for single-bit error correction
- Wide voltage range: 1.65 V to 2.2 V, 4.5 V to 5.5 V
- 1.0 V data retention
- Transistor-transistor logic (TTL) compatible inputs and outputs
- ERR pin to indicate 1-bit error detection and correction
- Available in Pb-free 48-ball VFBGA package

## Functional Description

CY62168G and CY62168GE are high-performance CMOS low-power (MoBL®) SRAM devices with embedded ECC. Both devices are offered in single and dual chip enable options and in multiple pin configurations. The CY62168GE device includes an error indication pin that signals a single-bit error-detection and correction event during a read cycle.

Devices with a single chip enable input are accessed by asserting the chip enable input (CE) LOW. Dual chip enable devices are accessed by asserting both chip enable inputs – CE<sub>1</sub> as LOW and CE<sub>2</sub> as HIGH.

Write to the device by taking Chip Enable 1 ( $\overline{CE}_1$ ) LOW and Chip Enable 2 (CE<sub>2</sub>) HIGH and the Write Enable (WE) input LOW. Data on the eight I/O pins (I/O<sub>0</sub> through I/O<sub>7</sub>) is then written into the location specified on the address pins (A<sub>0</sub> through A<sub>20</sub>).

Read from the device by taking Chip Enable 1 ( $\overline{CE}_1$ ) and Output Enable ( $\overline{OE}$ ) LOW and Chip Enable 2 (CE<sub>2</sub>) HIGH while forcing Write Enable (WE) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input and output pins (I/O<sub>0</sub> through I/O<sub>7</sub>) are placed in a high impedance state when the device is deselected ( $\overline{CE}_1$  HIGH or CE<sub>2</sub> LOW), the outputs are disabled ( $\overline{OE}$  HIGH), or a write operation is in progress ( $\overline{CE}_1$  LOW and CE<sub>2</sub> HIGH and WE LOW). See the [Truth Table – CY62168G/CY62168GE on page 14](#) for a complete description of read and write modes.

On CY62168GE devices, the detection and correction of a single bit error in the accessed location is indicated by the assertion of the ERR output (ERR = HIGH) [1].

The CY62168G and CY62168GE devices are available in a Pb-free 48-pin VFBGA package. The logic block diagrams are on page 2.

For a complete list of related resources, [click here](#).

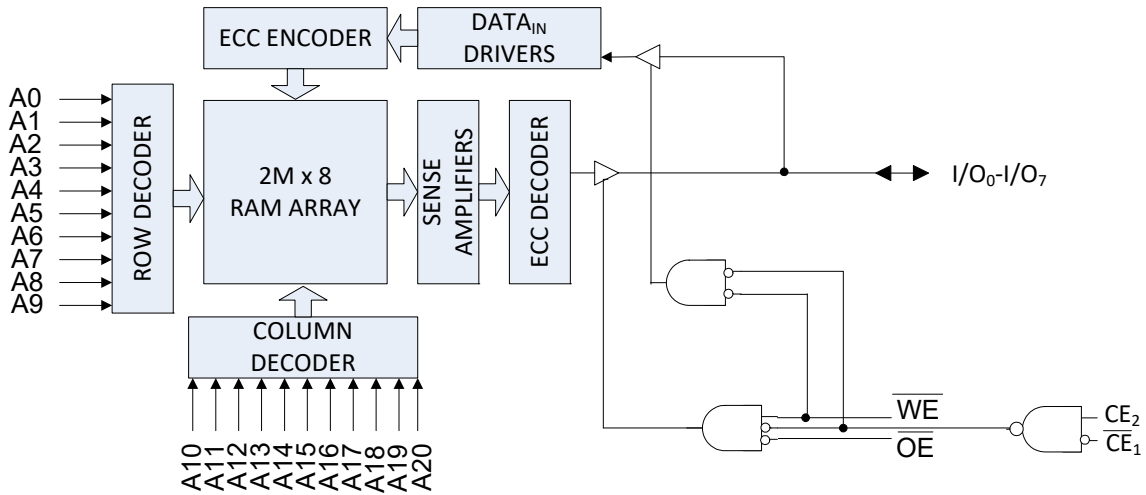
## Product Portfolio

Product	Features and Options (see <a href="#">Pin Configurations</a> section)	Range	V <sub>CC</sub> Range (V)	Speed (ns)	Power Dissipation			
					Operating I <sub>CC</sub> (mA)		Standby, I <sub>SB2</sub> ( $\mu$ A)	
					f = f <sub>max</sub>			
					Typ <sup>[2]</sup>	Max	Typ <sup>[2]</sup>	Max
CY62168G(E)18	Single or dual Chip Enables	Industrial	1.65 V–2.2 V	55	29	32	7	26
CY62168G(E)			4.5 V–5.5 V	45	29	36	5.5	16
	Optional ERR pin							

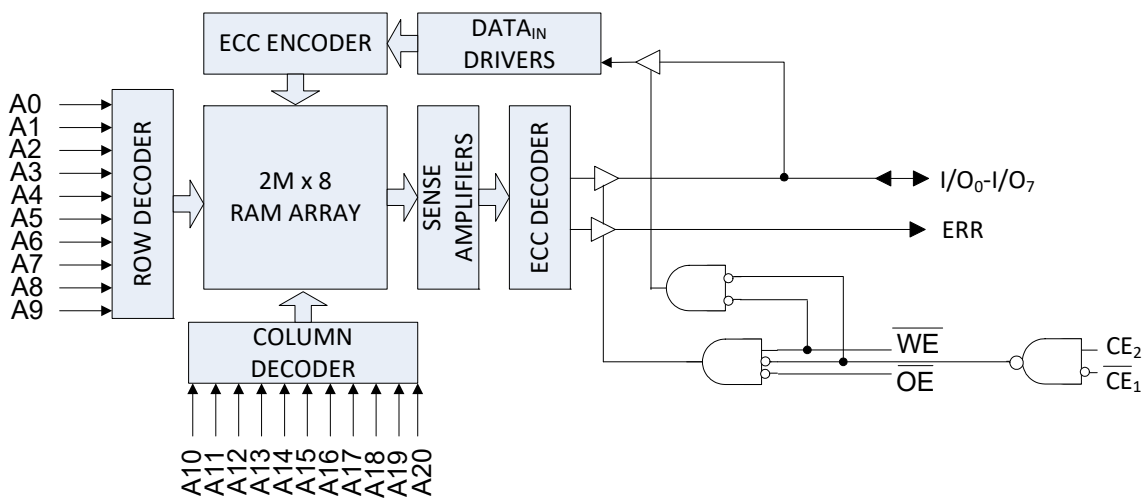
### Notes

1. This device does not support automatic write-back on error detection.
2. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = 1.8 V (for V<sub>CC</sub> range of 1.65 V–2.2 V), V<sub>CC</sub> = 3 V (for V<sub>CC</sub> range of 2.2 V–3.6 V), and V<sub>CC</sub> = 5 V (for V<sub>CC</sub> range of 4.5 V–5.5 V), T<sub>A</sub> = 25 °C.

Logic Block Diagram – CY62168G



Logic Block Diagram – CY62168GE



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## Pin Configurations

Figure 1. 48-ball VFBGA (6 × 8 × 1 mm) pinout<sup>[3]</sup>  
CY62168G

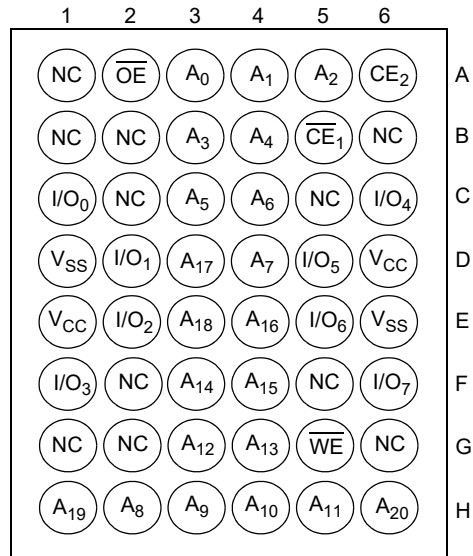
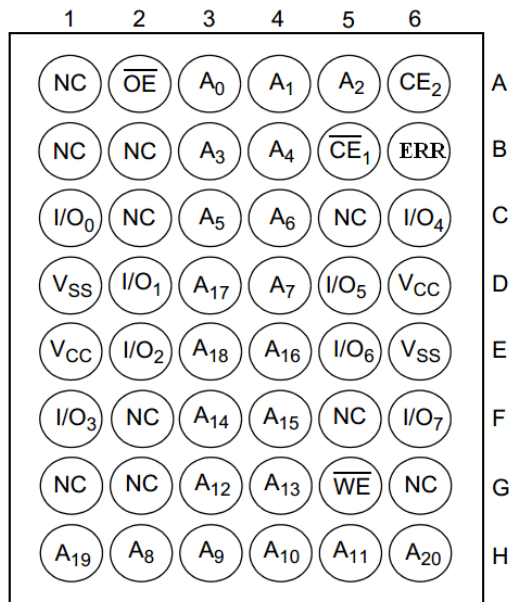


Figure 2. 48-ball VFBGA (6 × 8 × 1 mm) pinout<sup>[3, 4]</sup>  
CY62168GE



**Note**

3. NC pins are not connected internally to the die and are typically used for address expansion to a higher-density device. Refer to the respective datasheets for pin configuration.
4. ERR is an Output pin. If not used, this pin should be left floating.

## Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature ..... -65 °C to + 150 °C

Ambient temperature with power applied ..... -55 °C to + 125 °C

Supply voltage to ground potential ..... -0.5 V to 6 V

DC voltage applied to outputs in High Z state<sup>[5]</sup> ..... -0.5 V to  $V_{CC} + 0.5 V$

DC input voltage<sup>[5]</sup> ..... -0.5 V to  $V_{CC} + 0.5 V$

Output current into outputs (LOW) ..... 20 mA

Static discharge voltage (MIL-STD-883, Method 3015) ..... >2001 V

Latch-up current ..... >140 mA

## Operating Range

Grade	Ambient Temperature	$V_{CC}$ <sup>[6]</sup>
Industrial	-40 °C to +85 °C	1.65 V to 2.2 V, 4.5 V to 5.5 V

## DC Electrical Characteristics

Over the operating range of -40 °C to 85 °C

Parameter	Description	Test Conditions	45 ns/55 ns			Unit	
			Min	Typ <sup>[7]</sup>	Max		
$V_{OH}$	Output HIGH voltage	1.65 V to 2.2 V	$V_{CC} = \text{Min}, I_{OH} = -0.1 \text{ mA}$	1.4	-	-	V
		4.5 V to 5.5 V	$V_{CC} = \text{Min}, I_{OH} = -1.0 \text{ mA}$	2.4	-	-	V
		4.5 V to 5.5 V	$V_{CC} = \text{Min}, I_{OH} = -0.1 \text{ mA}$	$V_{CC} - 0.4$ <sup>[8]</sup>	-	-	V
$V_{OL}$	Output LOW voltage	1.65 V to 2.2 V	$V_{CC} = \text{Min}, I_{OL} = 0.1 \text{ mA}$	-	-	0.2	V
		4.5 V to 5.5 V	$V_{CC} = \text{Min}, I_{OL} = 2.1 \text{ mA}$	-	-	0.4	V
$V_{IH}$	Input HIGH voltage	1.65 V to 2.2 V	-	1.4	-	$V_{CC} + 0.2$	V
		4.5 V to 5.5 V	-	2.2	-	$V_{CC} + 0.5$	V
$V_{IL}$	Input LOW voltage <sup>[9]</sup>	1.65 V to 2.2 V	-	-0.2	-	0.4	V
		4.5 V to 5.5 V	-	-0.5	-	0.8	V
$I_{IX}$	Input leakage current	$GND \leq V_{IN} \leq V_{CC}$	-1.0	-	+1.0	$\mu\text{A}$	
$I_{OZ}$	Output leakage current	$GND \leq V_{OUT} \leq V_{CC}$ , Output disabled	-1.0	-	+1.0	$\mu\text{A}$	

### Notes

- $V_{IL(\text{min})} = -2.0 \text{ V}$  and  $V_{IH(\text{max})} = V_{CC} + 2 \text{ V}$  for pulse durations of less than 20 ns.
- Full Device AC operation assumes a 100  $\mu\text{s}$  ramp time from 0 to  $V_{CC(\text{min})}$  and 200  $\mu\text{s}$  wait time after  $V_{CC}$  stabilization.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at  $V_{CC} = 1.8 \text{ V}$  (for  $V_{CC}$  range of 1.65 V–2.2 V), and  $V_{CC} = 5 \text{ V}$  (for  $V_{CC}$  range of 4.5 V–5.5 V),  $T_A = 25 \text{ }^\circ\text{C}$ .
- This parameter is guaranteed by design and is not tested.
- $V_{IL(\text{min})} = -2.0 \text{ V}$  and  $V_{IH(\text{max})} = V_{CC} + 2 \text{ V}$  for pulse durations of less than 20 ns.

**DC Electrical Characteristics** (continued)

 Over the operating range of  $-40\text{ }^{\circ}\text{C}$  to  $85\text{ }^{\circ}\text{C}$ 

Parameter	Description	Test Conditions	45 ns/55 ns			Unit	
			Min	Typ <sup>[7]</sup>	Max		
$I_{CC}$	$V_{CC}$ operating supply current	$V_{CC} = \text{Max}$ , $I_{OUT} = 0\text{ mA}$ , CMOS levels	$f = 22.22\text{ MHz}$ (45 ns)	–	29.0	36.0	mA
			$f = 18.18\text{ MHz}$ (55 ns)	–	29.0	32.0	mA
			$f = 1\text{ MHz}$	–	7.0	9.0	mA
$I_{SB1}^{[10]}$	Automatic power down current – CMOS inputs; $V_{CC} = 4.5\text{ V}$ to $5.5\text{ V}$	$\overline{CE}_1 \geq V_{CC} - 0.2\text{ V}$ or $CE_2 \leq 0.2\text{ V}$ , $V_{IN} \geq V_{CC} - 0.2\text{ V}$ , $V_{IN} \leq 0.2\text{ V}$ , $f = f_{\text{max}}$ (address and data only),	–	5.5	16.0	$\mu\text{A}$	
	Automatic power down current – CMOS inputs; $V_{CC} = 1.65$ to $2.2\text{ V}$	$f = 0$ ( $\overline{OE}$ , and $\overline{WE}$ ), $V_{CC} = V_{CC(\text{max})}$	–	7	26.0	$\mu\text{A}$	
$I_{SB2}^{[10]}$	Automatic power down current – CMOS inputs; $V_{CC} = 4.5\text{ V}$ to $5.5\text{ V}$	$\overline{CE}_1 \geq V_{CC} - 0.2\text{ V}$ or $CE_2 \leq 0.2\text{ V}$ ,	$25\text{ }^{\circ}\text{C}$ [11]	–	5.5	6.5	$\mu\text{A}$
			$40\text{ }^{\circ}\text{C}$ [11]	–	6.3	8.0	$\mu\text{A}$
		$V_{IN} \geq V_{CC} - 0.2\text{ V}$ or $V_{IN} \leq 0.2\text{ V}$ ,	$70\text{ }^{\circ}\text{C}$ [11]	–	8.4	12.0	$\mu\text{A}$
			$85\text{ }^{\circ}\text{C}$	–	12.0 [11]	16.0	$\mu\text{A}$
	Automatic power down current – CMOS inputs; $V_{CC} = 1.65$ to $2.2\text{ V}$	$\overline{CE}_1 \geq V_{CC} - 0.2\text{ V}$ or $CE_2 \leq 0.2\text{ V}$ , $V_{IN} \geq V_{CC} - 0.2\text{ V}$ or $V_{IN} \leq 0.2\text{ V}$ , $f = 0$ , $V_{CC} = V_{CC(\text{max})}$	–	7.0	26.0	$\mu\text{A}$	

**Notes**

10. Chip enables ( $\overline{CE}_1$  and  $CE_2$ ) must be tied to CMOS levels to meet the  $I_{SB1}/I_{SB2}/I_{CCDR}$  spec. Other inputs can be left floating.  
 11. The  $I_{SB2}$  limits at  $25\text{ }^{\circ}\text{C}$ ,  $40\text{ }^{\circ}\text{C}$ ,  $70\text{ }^{\circ}\text{C}$  and typical limit at  $85\text{ }^{\circ}\text{C}$  are guaranteed by design and not 100% tested.

### Capacitance

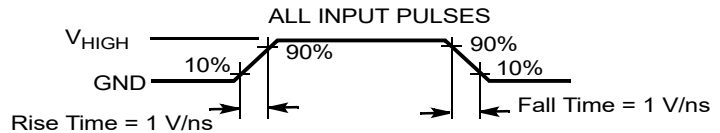
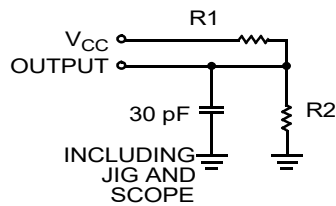
Parameter <sup>[12]</sup>	Description	Test Conditions	Max	Unit
C <sub>IN</sub>	Input capacitance	T <sub>A</sub> = 25 °C, f = 1 MHz, V <sub>CC</sub> = V <sub>CC(typ)</sub>	10	pF
C <sub>OUT</sub>	Output capacitance		10	pF

### Thermal Resistance

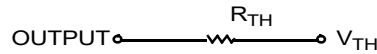
Parameter <sup>[12]</sup>	Description	Test Conditions	48-ball VFBGA	Unit
θ <sub>JA</sub>	Thermal resistance (junction to ambient)	Still air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	31.50	°C/W
θ <sub>JC</sub>	Thermal resistance (junction to case)		15.75	°C/W

### AC Test Loads and Waveforms

Figure 3. AC Test Loads and Waveforms



Equivalent to: THÉVENIN EQUIVALENT



Parameters	1.8 V	2.5 V	3.0 V	5.0 V	Unit
R1	13500	16667	1103	1800	Ω
R2	10800	15385	1554	990	Ω
R <sub>TH</sub>	6000	8000	645	639	Ω
V <sub>TH</sub>	0.8	1.2	1.75	1.77	V
V <sub>HIGH</sub>	1.8	2.5	3.0	5.0	V

**Note**

12. Tested initially and after any design or process changes that may affect these parameters.



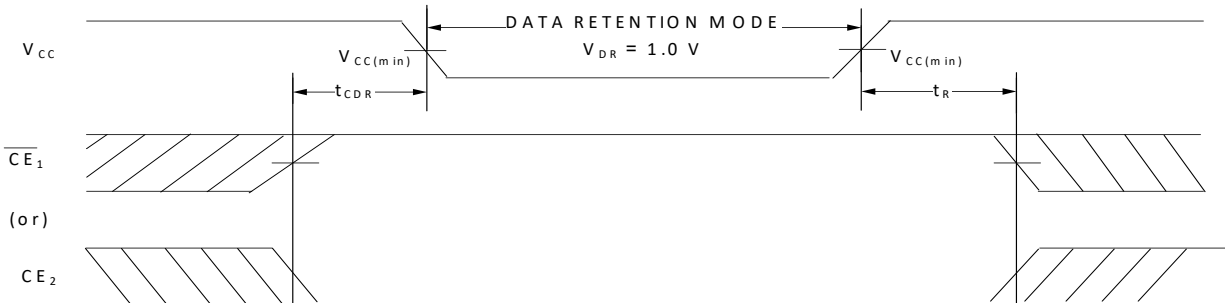
### Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Min	Typ <sup>[13]</sup>	Max	Unit
$V_{DR}$	$V_{CC}$ for data retention		1.0	–	–	V
$I_{CCDR}$ <sup>[14, 15]</sup>	Data retention current	$1.2\text{ V} \leq V_{CC} \leq 2.2\text{ V}$ , $\overline{CE}_1 \geq V_{CC} - 0.2\text{ V}$ or $CE_2 \leq 0.2\text{ V}$ , $V_{IN} \geq V_{CC} - 0.2\text{ V}$ or $V_{IN} \leq 0.2\text{ V}$	–	7.0	26.0	$\mu\text{A}$
		$4.5\text{ V} \leq V_{CC} \leq 5.5\text{ V}$ , $\overline{CE}_1 \geq V_{CC} - 0.2\text{ V}$ or $CE_2 \leq 0.2\text{ V}$ , $V_{IN} \geq V_{CC} - 0.2\text{ V}$ or $V_{IN} \leq 0.2\text{ V}$	–	5.5	16.0	$\mu\text{A}$
$t_{CDR}$ <sup>[16]</sup>	Chip deselect to data retention time		0	–	–	–
$t_R$ <sup>[16, 17]</sup>	Operation recovery time		45/55	–	–	ns

### Data Retention Waveform

Figure 4. Data Retention Waveform



**Notes**

- 13. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at  $V_{CC} = 1.8\text{ V}$  (for  $V_{CC}$  range of 1.65 V–2.2 V), and  $V_{CC} = 5\text{ V}$  (for  $V_{CC}$  range of 4.5 V–5.5 V),  $T_A = 25\text{ }^\circ\text{C}$ .
- 14. Chip enables ( $\overline{CE}_1$  and  $CE_2$ ) must be tied to CMOS levels to meet the  $I_{SB1}/I_{SB2}/I_{CCDR}$  spec. Other inputs can be left floating.
- 15.  $I_{CCDR}$  is guaranteed only after device is first powered up to  $V_{CC(min)}$  and brought down to  $V_{DR}$ .
- 16. These parameters are guaranteed by design.
- 17. Full device operation requires linear  $V_{CC}$  ramp from  $V_{DR}$  to  $V_{CC(min)} \geq 100\text{ }\mu\text{s}$  or stable at  $V_{CC(min)} \geq 100\text{ }\mu\text{s}$ .

## Switching Characteristics

Parameter <sup>[18, 19]</sup>	Description	45 ns		55 ns		Unit
		Min	Max	Min	Max	
<b>Read Cycle</b>						
$t_{RC}$	Read cycle time	45.0	–	55.0	–	ns
$t_{AA}$	Address to data valid / Address to ERR valid	–	45.0	–	55.0	ns
$t_{OHA}$	Data hold from address change / ERR hold from address change	10.0	–	10.0	–	ns
$t_{ACE}$	$\overline{CE}_1$ LOW and $CE_2$ HIGH to data valid / $\overline{CE}$ LOW to ERR valid	–	45.0	–	55.0	ns
$t_{DOE}$	$\overline{OE}$ LOW to data valid / $\overline{OE}$ LOW to ERR valid	–	22.0	–	25.0	ns
$t_{LZOE}$	$\overline{OE}$ LOW to Low Z <sup>[19, 20]</sup>	5.0	–	5.0	–	ns
$t_{HZOE}$	$\overline{OE}$ HIGH to High Z <sup>[19, 20, 21]</sup>	–	18.0	–	18.0	ns
$t_{LZCE}$	$\overline{CE}_1$ LOW and $CE_2$ HIGH to Low Z <sup>[19, 20]</sup>	10.0	–	10.0	–	ns
$t_{HZCE}$	$\overline{CE}_1$ HIGH and $CE_2$ LOW to High Z <sup>[19, 20, 21]</sup>	–	18.0	–	18.0	ns
$t_{PU}$ <sup>[22]</sup>	$\overline{CE}_1$ LOW and $CE_2$ HIGH to power-up	0	–	0	–	ns
$t_{PD}$ <sup>[22]</sup>	$\overline{CE}_1$ HIGH and $CE_2$ LOW to power-down	–	45.0	–	55.0	ns
<b>Write Cycle</b> <sup>[23, 24]</sup>						
$t_{WC}$	Write cycle time	45.0	–	55.0	–	ns
$t_{SCE}$	$\overline{CE}_1$ LOW and $CE_2$ HIGH to write end	35.0	–	40.0	–	ns
$t_{AW}$	Address setup to write end	35.0	–	40.0	–	ns
$t_{HA}$	Address hold from write end	0	–	0	–	ns
$t_{SA}$	Address setup to write start	0	–	0	–	ns
$t_{PWE}$	$\overline{WE}$ pulse width	35.0	–	40.0	–	ns
$t_{SD}$	Data setup to write end	25.0	–	25.0	–	ns
$t_{HD}$	Data hold from write end	0	–	0	–	ns
$t_{HZWE}$	$\overline{WE}$ LOW to High Z <sup>[19, 21, 20]</sup>	–	18.0	–	20.0	ns
$t_{LZWE}$	$\overline{WE}$ HIGH to Low Z <sup>[19, 20]</sup>	10.0	–	10.0	–	ns

### Notes

18. Test conditions assume signal transition time (rise/fall) of 3 ns or less, timing reference levels of 1.5 V (for  $V_{CC} \geq 3$  V) and  $V_{CC}/2$  (for  $V_{CC} < 3$  V), and input pulse levels of 0 to 3 V (for  $V_{CC} \geq 3$  V) and 0 to  $V_{CC}$  (for  $V_{CC} < 3$  V). Test conditions for the read cycle use output loading shown in AC Test Loads and Waveforms section, unless specified otherwise.

19. At any temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any device.

20. Tested initially and after any design or process changes that may affect these parameters.

21.  $t_{HZOE}$ ,  $t_{HZCE}$ , and  $t_{HZWE}$  transitions are measured when the outputs enter a high impedance state.

22. These parameters are guaranteed by design and are not tested.

23. The internal write time of the memory is defined by the overlap of  $\overline{WE} = V_{IL}$ ,  $\overline{CE}_1 = V_{IL}$ , and  $CE_2 = V_{IH}$ . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.

24. The minimum write cycle pulse width for write cycle No. 2 ( $\overline{WE}$  Controlled,  $\overline{OE}$  Low) should be equal to the sum of  $t_{HZWE}$  and  $t_{SD}$ .

## Switching Waveforms

Figure 5. Read Cycle No. 1 of CY62168G (Address Transition Controlled)<sup>[25, 26]</sup>

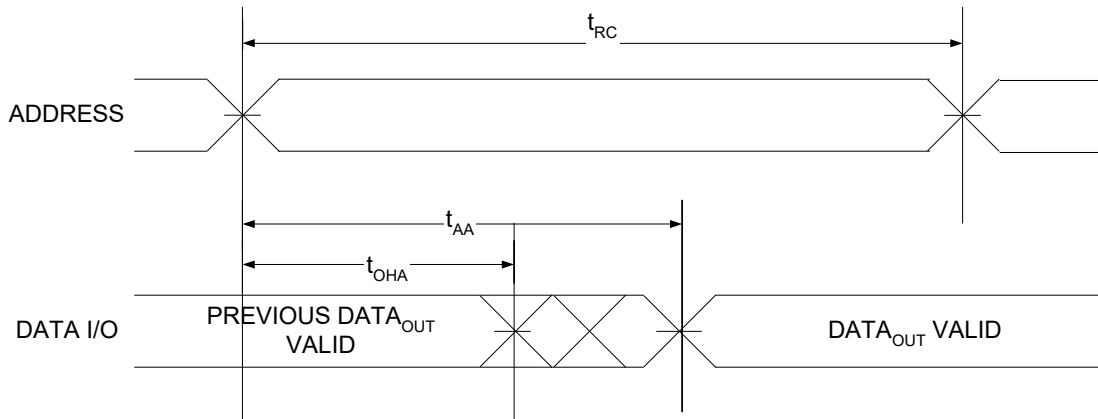
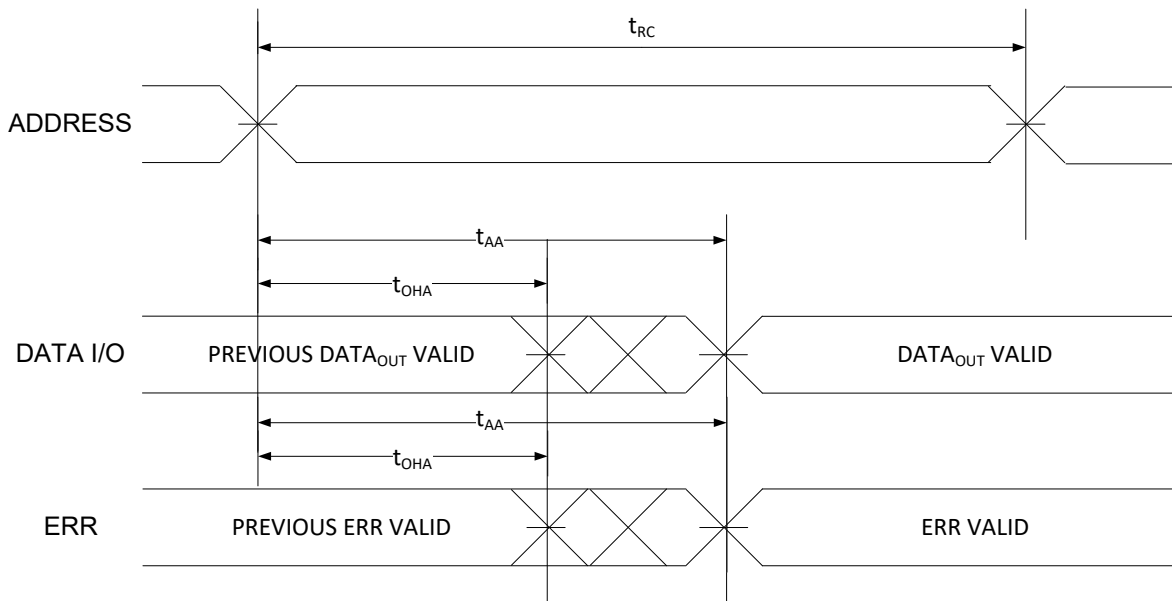


Figure 6. Read Cycle No. 1 of CY62168GE (Address Transition Controlled)<sup>[25, 26]</sup>

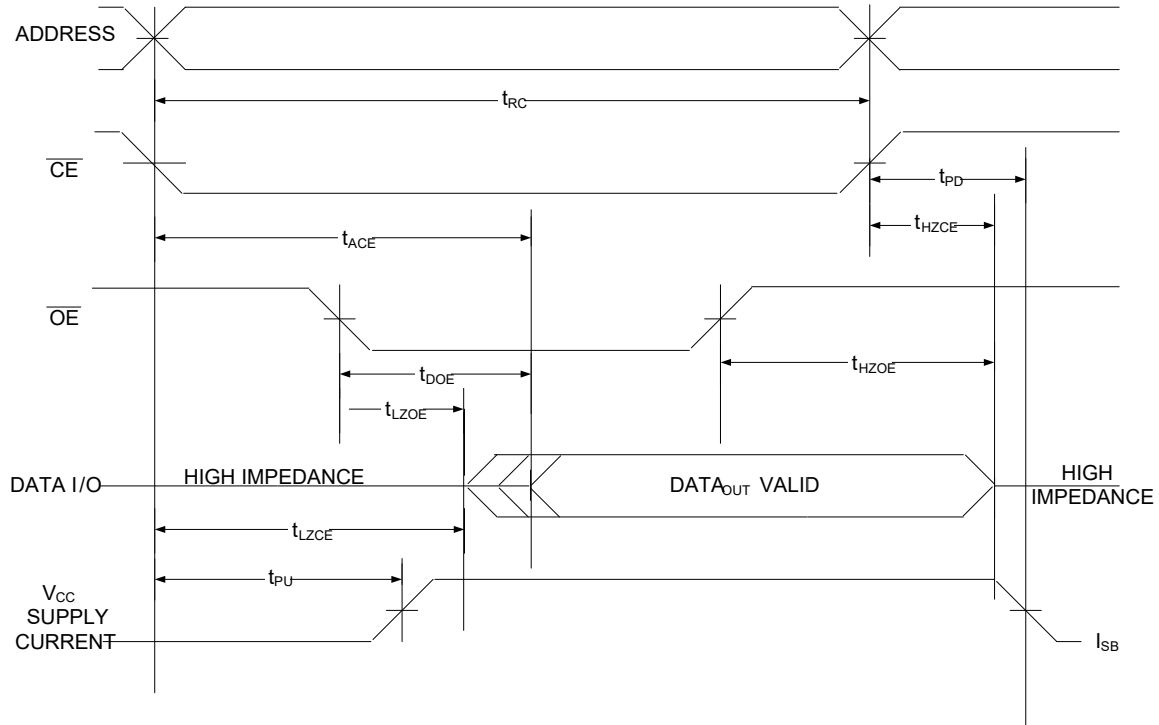


### Notes

25. The device is continuously selected.  $\overline{OE} = V_{IL}$ ,  $\overline{CE} = V_{IL}$ .  
 26. WE is HIGH for read cycle.

Switching Waveforms (continued)

Figure 7. Read Cycle No. 2 ( $\overline{OE}$  Controlled)<sup>[27, 28, 29]</sup>

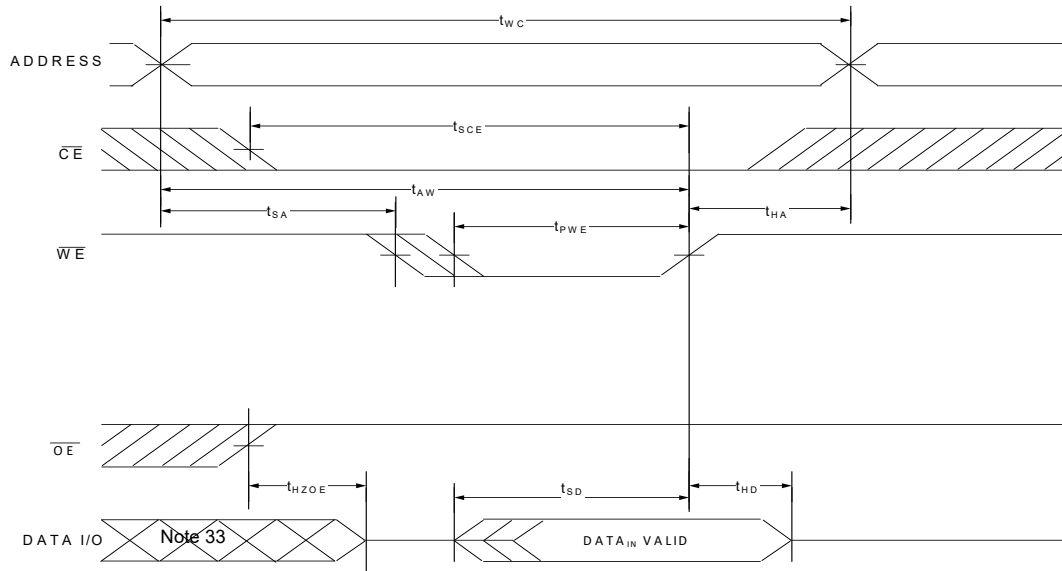


Notes

- 27.  $\overline{WE}$  is HIGH for read cycle.
- 28. For all dual chip enable devices,  $\overline{CE}$  is the logical combination of  $\overline{CE}_1$  and  $CE_2$ . When  $\overline{CE}_1$  is LOW and  $CE_2$  is HIGH,  $\overline{CE}$  is LOW; when  $\overline{CE}_1$  is HIGH or  $CE_2$  is LOW,  $\overline{CE}$  is HIGH.
- 29. Address valid prior to or coincident with  $\overline{CE}$  LOW transition.

Switching Waveforms (continued)

Figure 8. Write Cycle No. 1 ( $\overline{WE}$  Controlled)<sup>[30, 31, 32]</sup>



Notes

- 30. For all dual chip enable devices,  $\overline{CE}$  is the logical combination of  $\overline{CE}_1$  and  $CE_2$ . When  $\overline{CE}_1$  is LOW and  $CE_2$  is HIGH,  $\overline{CE}$  is LOW; when  $\overline{CE}_1$  is HIGH or  $CE_2$  is LOW,  $\overline{CE}$  is HIGH.
- 31. The internal write time of the memory is defined by the overlap of  $\overline{WE} = V_{IL}$ ,  $\overline{CE}_1 = V_{IL}$ , and  $CE_2 = V_{IH}$ . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
- 32. Data I/O is in the high-impedance state if  $\overline{CE} = V_{IH}$  or  $\overline{OE} = V_{IH}$ .
- 33. During this period, the I/Os are in output state. Do not apply input signals.

Switching Waveforms (continued)

Figure 9. Write Cycle No. 2 ( $\overline{WE}$  Controlled,  $\overline{OE}$  Low)<sup>[34, 35, 36, 37]</sup>

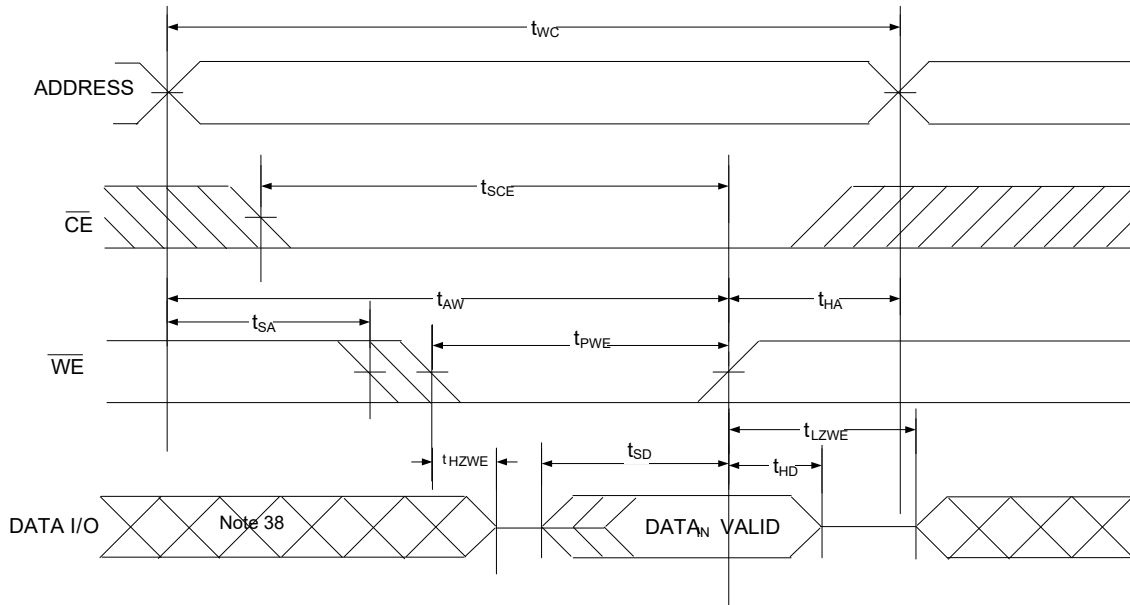
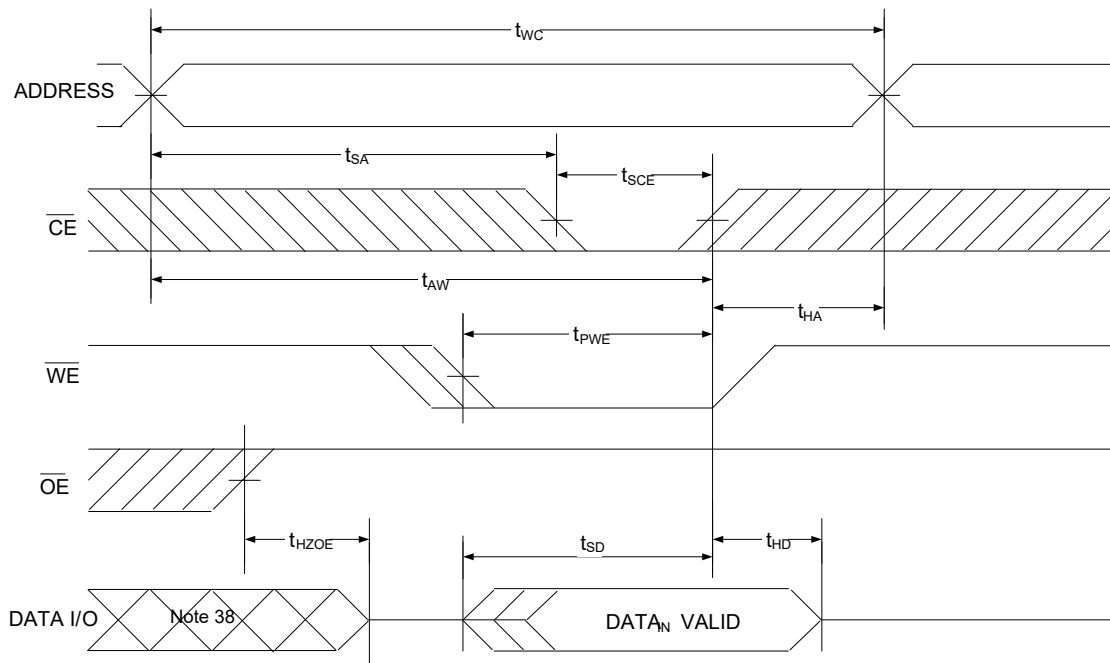


Figure 10. Write Cycle No. 3 ( $\overline{CE}$  Controlled)<sup>[34, 35, 36]</sup>



Notes

- 34. For all dual chip enable devices,  $\overline{CE}$  is the logical combination of  $\overline{CE}_1$  and  $CE_2$ . When  $\overline{CE}_1$  is LOW and  $CE_2$  is HIGH,  $\overline{CE}$  is LOW; when  $\overline{CE}_1$  is HIGH or  $CE_2$  is LOW,  $\overline{CE}$  is HIGH.
- 35. The internal write time of the memory is defined by the overlap of  $\overline{WE} = V_{IL}$ ,  $\overline{CE}_1 = V_{IL}$ , and  $CE_2 = V_{IH}$ . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
- 36. Data I/O is in high impedance state if  $\overline{CE} = V_{IH}$  or  $\overline{OE} = V_{IH}$ .
- 37. The minimum write cycle pulse width should be equal to the sum of the  $t_{HZWE}$  and  $t_{SD}$ .
- 38. During this period I/O are in the output state. Do not apply input signals.

**Truth Table – CY62168G/CY62168GE**

$\overline{CE}_1$	$CE_2$	$\overline{WE}$	$\overline{OE}$	I/Os	Mode	Power
H	X <sup>[39]</sup>	X <sup>[39]</sup>	X <sup>[39]</sup>	High Z	Deselect/Power down	Standby (I <sub>SB2</sub> )
X <sup>[39]</sup>	L	X <sup>[39]</sup>	X <sup>[39]</sup>	High Z	Deselect/Power down	Standby (I <sub>SB2</sub> )
L	H	H	L	Data Out (I/O <sub>0</sub> –I/O <sub>7</sub> )	Read	Active (I <sub>CC</sub> )
L	H	H	H	High Z	Output disabled	Active (I <sub>CC</sub> )
L	H	L	X	Data In (I/O <sub>0</sub> –I/O <sub>7</sub> )	Write	Active (I <sub>CC</sub> )

**ERR Output – CY62168GE**

Output <sup>[40]</sup>	Mode
0	Read Operation, no single-bit error in the stored data.
1	Read Operation, single-bit error detected and corrected.
High Z	Device deselected/Outputs disabled/Write Operation.

**Note**

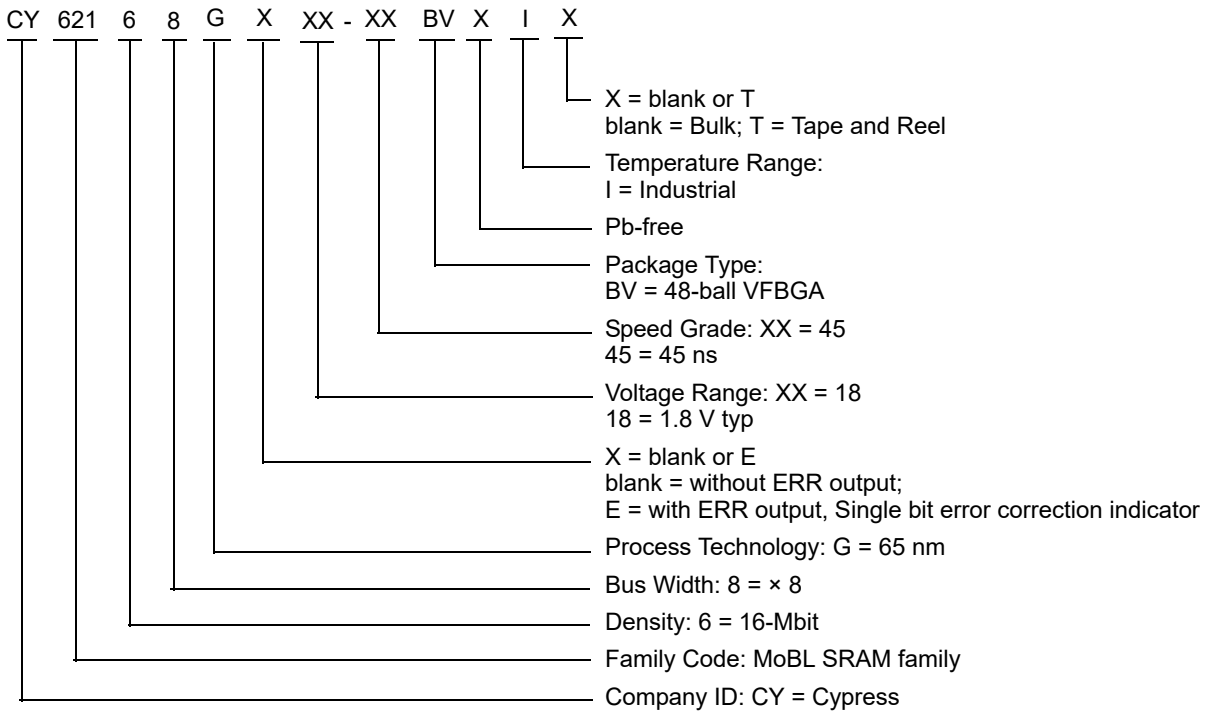
39. The 'X' (Don't care) state for the chip enables refer to the logic state (either HIGH or LOW). Intermediate voltage levels on these pins is not permitted.

40. ERR is an Output pin. If not used, this pin should be left floating.

### Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type (all Pb-free)	Operating Range
55	CY62168G18-55BVXI	51-85150	48-ball VFBGA	Industrial
	CY62168G18-55BVXIT		48-ball VFBGA, Tape and Reel	

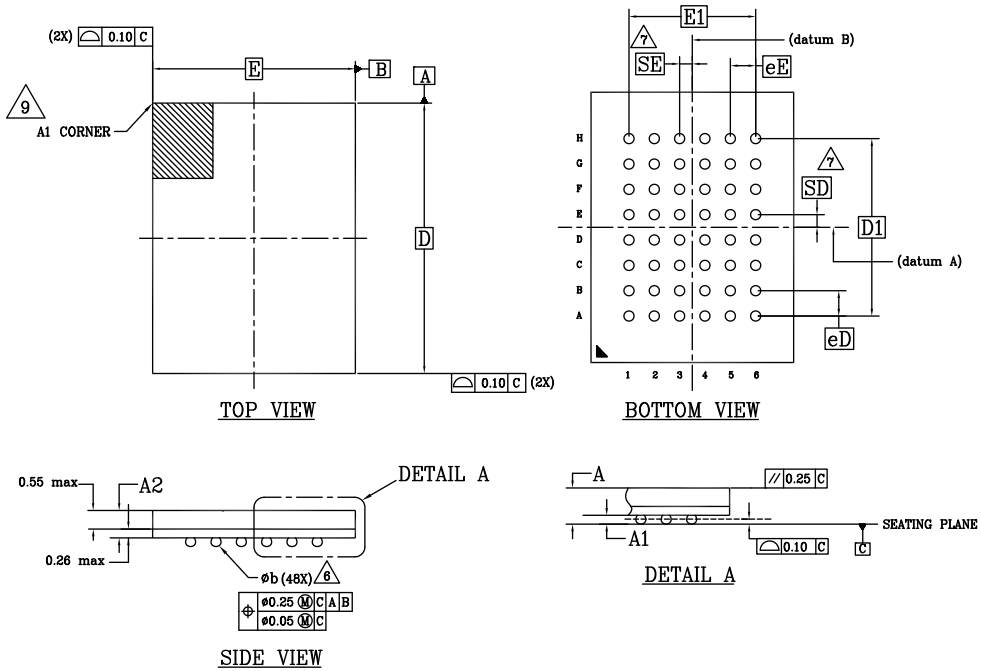
### Ordering Code Definitions





Package Diagrams

Figure 11. 48-ball VFBGA (6 × 8 × 1.0 mm) Package Outline, 51-85150



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	-	-	1.00
A1	0.16	-	-
A2	-	-	0.81
D	8,00 BSC		
E	6,00 BSC		
D1	5,25 BSC		
E1	3,75 BSC		
MD	8		
ME	6		
n	48		
$\phi b$	0,25	0,30	0,35
eE	0,75 BSC		
eD	0,75 BSC		
SD	0,375 BSC		
SE	0,375 BSC		

NOTES:

- DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-2009.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-020.
- ☐ REPRESENTS THE SOLDER BALL GRID PITCH.
- SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION, SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION. n IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
- DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
- "SD" AND "SE" ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW. WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW "SD" OR "SE" = 0. WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" = eD/2 AND "SE" = eE/2.
- "\*" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
- A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK METALIZED MARK, INDENTATION OR OTHER MEANS.

51-85150 \*I

## Acronyms

Acronym	Description
$\overline{CE}$	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
$\overline{OE}$	Output Enable
SRAM	Static Random Access Memory
VFBGA	Very Fine-Pitch Ball Grid Array
$\overline{WE}$	Write Enable

## Document Conventions

### Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μA	microampere
μs	microsecond
mA	milliampere
mm	millimeter
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt

Document History Page

Document Title: CY62168G/CY62168GE MoBL, 16-Mbit (2M words × 8 bits) Static RAM with Error-Correcting Code (ECC) Document Number: 001-84771			
Rev.	ECN No.	Submission Date	Description of Change
*G	4800984	07/31/2015	Changed status from Preliminary to Final.
*H	5449003	11/03/2016	<p>Updated <a href="#">Maximum Ratings</a>:            Updated Note 5 (Replaced “2 ns” with “20 ns”).            Updated <a href="#">DC Electrical Characteristics</a>:            Changed minimum value of V<sub>OH</sub> parameter from 2.2 V to 2.4 V corresponding to Operating Range “2.7 V to 3.6 V”.            Changed minimum value of V<sub>IH</sub> parameter from 2.0 V to 1.8 V corresponding to Operating Range “2.2 V to 2.7 V”.            Updated <a href="#">Thermal Resistance</a>:            Replaced “two-layer” with “four-layer” in “Test Conditions” column.            Updated <a href="#">Ordering Information</a>:            Updated part numbers.            Updated <a href="#">Ordering Code Definitions</a>.            Updated to new template.            Completing Sunset Review.</p>
*I	6003639	12/22/2017	Updated Cypress Logo and Copyright.
*J	6673157	09/25/2019	<p>Updated <a href="#">Product Portfolio</a>:            Added Note “This device is offered with improved I<sub>CC</sub>, I<sub>SB1</sub> and I<sub>SB2</sub> specifications compared to the current revision with same marketing part number. The new device will be in production from WW1952. For more information, please contact Cypress sales representative.” and referred the same note in “CY62168G(E)30”.            Added Note “For next version of this device, kindly refer <a href="#">here</a>. Further details about improvement and comparison between current and new versions can be found in the <a href="#">PCN193805</a>.” and referred the same note in “CY62168G(E)30”.            Updated <a href="#">DC Electrical Characteristics</a>:            Added Note “This device is offered with improved I<sub>CC</sub>, I<sub>SB1</sub> and I<sub>SB2</sub> specifications compared to the current revision with same marketing part number. The new device will be in production from WW1952. For more information, please contact Cypress sales representative.” and referred the same note in I<sub>CC</sub>, I<sub>SB1</sub>, I<sub>SB2</sub> parameters.            Added Note “For next version of this device, kindly refer <a href="#">here</a>. Further details about improvement and comparison between current and new versions can be found in the <a href="#">PCN193805</a>.” and referred the same note in I<sub>CC</sub>, I<sub>SB1</sub>, I<sub>SB2</sub> parameters.            Updated <a href="#">Data Retention Characteristics</a>:            Added Note “This device is offered with improved I<sub>CC</sub>, I<sub>SB1</sub> and I<sub>SB2</sub> specifications compared to the current revision with same marketing part number. The new device will be in production from WW1952. For more information, please contact Cypress sales representative.” and referred the same note in I<sub>CCDR</sub> parameter.            Added Note “For next version of this device, kindly refer <a href="#">here</a>. Further details about improvement and comparison between current and new versions can be found in the <a href="#">PCN193805</a>.” and referred the same note in I<sub>CCDR</sub> parameter.            Updated <a href="#">Package Diagrams</a>:            spec 51-85150 – Changed revision from *H to *I.            Updated to new template.</p>

**Document History Page** (continued)

Document Title: CY62168G/CY62168GE MoBL, 16-Mbit (2M words × 8 bits) Static RAM with Error-Correcting Code (ECC) Document Number: 001-84771			
Rev.	ECN No.	Submission Date	Description of Change
*K	6816924	02/26/2020	Removed CY62168G(E)30 part related information in all instances across the document. Removed 2.2 V to 3.6 V Voltage Range related information in all instances across the document. Updated <a href="#">Ordering Information</a> : Updated part numbers. Updated <a href="#">Ordering Code Definitions</a> . Updated to new template. Completing Sunset Review.

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